

SEMiX 191KD ...



SEMiX® 1s

Rectifier Diode Module

SEMiX 191KD

Target Data

Features

- terminal height of 17mm
- chip solder on direct copper bonded Al_2O_3 ceramic
- heat transfer through Al_2O_3 ceramic isolated baseplate

Typical Applications

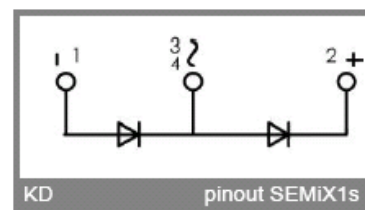
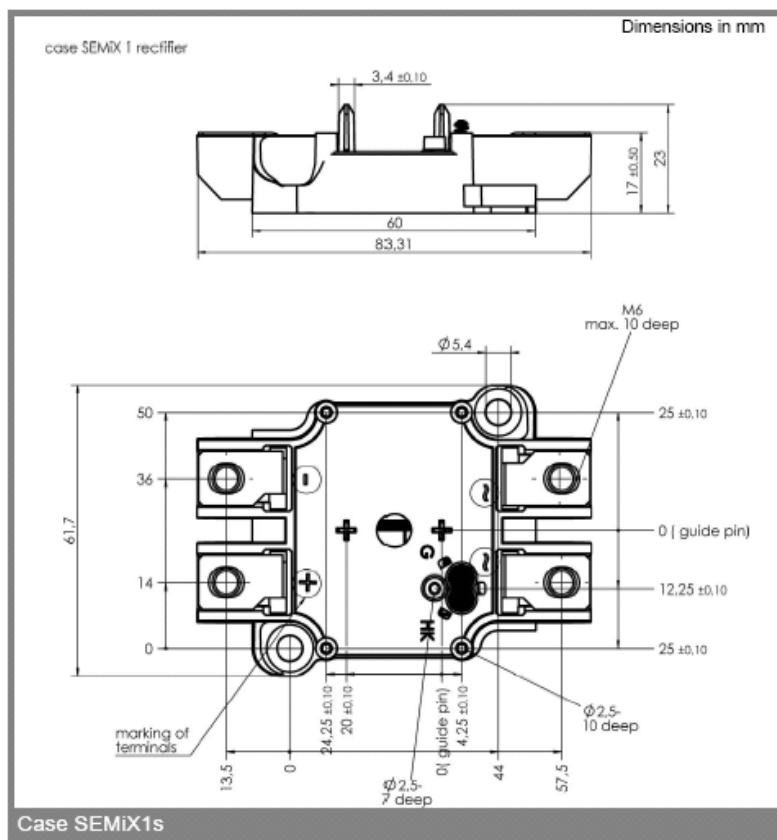
- Input Bridge Rectifier for
- AC/DC motor control
- power supply

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 285 \text{ A}$ (maximum value for continuous operation) $I_{FAV} = 190 \text{ A}$ (sin. 180; $T_c = 85^\circ\text{C}$)		
1700	1600	SEMiX 191KD16s		

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85$ (100) $^\circ\text{C}$	190 (145)	A
I_{FSM}	$T_{vj} = 25^\circ\text{C}$; 10 ms $T_{vj} = 130^\circ\text{C}$; 10 ms	6000 5000	A
P_t	$T_{vj} = 25^\circ\text{C}$; 8,3 ... 10 ms $T_{vj} = 130^\circ\text{C}$; 8,3 ... 10 ms	180000 125000	A^2s A^2s
V_F	$T_{vj} = 25^\circ\text{C}$; $I_F = 500 \text{ A}$	max. 1,5	V
$V_{(TO)}$	$T_{vj} = 130^\circ\text{C}$	max. 0,85	V
r_T	$T_{vj} = 130^\circ\text{C}$	max. 0,95	$\text{m}\Omega$
I_{RD}	$T_{vj} = 130^\circ\text{C}$; $V_{RD} = V_{RRM}$	max. 12	mA
$R_{th(j-c)}$	per diode	0,18	K/W
$R_{th(c-s)}$	per module	0,075	K/W
T_{vj}		- 40 ... + 130	$^\circ\text{C}$
T_{stg}		- 40 ... + 125	$^\circ\text{C}$
V_{isol}	AC, 50Hz.; rms; 1s/1min	4800 / 4000	V~
M_s	(min./max.)	3/5	Nm
M_t	(min./max.)	2,5/5	Nm
a		5 * 9,81	m/s^2
m	approx.	145	g
Case	SEMiX 1s		



KD



This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.